

AMENDMENT TO THE CLAIMS

1. (Currently Amended) A method comprising:
selecting a dicing tape with an adhesive layer that has a thickness greater than a height of one or more bump electrodes formed on a first side of a wafer;
applying the dicing tape to the first side of the wafer such that the adhesive layer contacts and conforms to the one or more bump electrodes; and
dicing the wafer from a second side of the wafer opposite the first side, the dicing extending into the adhesive layer a distance less than a thickness of the adhesive layer.
2. (Previously Presented) The method of claim 1 wherein the wafer is a double bumped wafer with bump electrodes formed on the second side.
3. (Original) The method of claim 2 wherein the dicing tape is applied using a mounting pressure roller wherein the adhesive layer helps to distribute a pressure applied by the mounting pressure roller.
4. (Previously Presented) The method of claim 3 further comprising:
after dicing, reducing an adhesive strength of the adhesive layer by exposing the adhesive layer to radiation.
5. (Original) The method of claim 4 wherein the bump electrodes have a height of approximately 60 microns and the adhesive layer has a thickness of approximately 130 microns.
6. (Previously Presented) The method of claim 5, wherein dicing comprises:
dicing the wafer using a dual-blade dicing process wherein a first blade dices through less than an entire thickness of the wafer followed by a second blade that dices through the wafer.
7. (Canceled)

8. (Previously Presented) The method of claim 4 wherein the adhesive strength is reduced from a pre-radiation adhesive strength of approximately 200 grams/25 mm² to a post-radiation adhesive strength of approximately 2 grams/25 mm².

9-13 (Canceled)

14. (Currently Amended) A method comprising:
determining a height of one or more bump electrodes on a first side of a wafer surface;
selecting a dicing tape based upon the determined height of the one or more bump electrodes, a first side of the dicing tape comprising an adhesive layer thicker than the determined height of the one or more bump electrodes;
applying the first side of the dicing tape to the first side of the wafer such that the adhesive layer contacts and conforms to the one or more bump electrodes; and
dicing the wafer from a second side of the wafer opposite the first side, the dicing extending into the adhesive layer a distance less than a thickness of the adhesive layer.

15. (Original) The method of claim 14 wherein the wafer is a double bumped wafer.

16-17. (Canceled)

18. (Previously Presented) The method of claim 14 wherein the dicing tape is applied using a mounting pressure roller wherein the adhesive layer helps to distribute a pressure applied by the mounting pressure roller.

19. (Original) The method of claim 14 wherein the dicing tape is a radiation sensitive tape having a pre-radiation adhesive strength of approximately 200 grams/25 mm², and a post-radiation adhesive strength of approximately 2 grams/25 mm².

20. (Original) The method of claim 14 wherein the bump electrodes have a height of approximately 60 microns and the adhesive layer has a thickness of approximately 130 microns.

21. (Previously Presented) The method of claim 20 further comprising:
dicing the wafer using a dual-blade dicing process.
22. (Previously Presented) The method of claim 21 further comprising:
wherein reducing an adhesive strength comprises irradiating a second side of the dicing
tape.
- 23-27 (Canceled)